AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-11. (Cancelled)

12. (Original) A method for fabricating a light-emitting device, the method comprising:

(a) sequentially forming a first compound semiconductor layer, an active layer, and a second compound semiconductor layer, which are for inducing light emission, on a high-resistant substrate;

(b) forming a light-reflecting conductive layer on the second compound semiconductor layer;

(c) etching a region of the high-resistant substrate to expose the first compound semiconductor layer; and

(d) forming a light-transmitting conductive layer to cover the exposed region of the first compound semiconductor layer.

13. (Original) The method of claim 12, wherein step (c) comprises:

polishing the bottom of the high-resistant substrate; and

exposing the bottom of the first compound semiconductor layer by etching the region of the high-resistant substrate.

14. (Original) The method of claim 13, wherein the high-resistant substrate is a sapphire substrate.

15. (Original) The method of claim 13, wherein the bottom of the high-resistant substrate is polished by grinding or lapping.

16. (Currently Amended) A method for fabricating a light-emitting device, the method comprising:

(a) sequentially forming a first compound semiconductor layer, an active layer, and a second compound semiconductor layer, which are for inducing light emission, on a high-resistant substrate;

(b) forming a light-reflecting conductive layer on the second compound semiconductor layer;

(c) etching a region of the high-resistant substrate to expose the first compound semiconductor layer; and

(d) forming a light-transmitting conductive layer to cover the exposed region of the first compound semiconductor layer, ~~The method of claim 12,~~

wherein the high-resistant substrate is dry etched using a reaction gas comprising at least Cl_2 or BCl_3.

17. (Original) The method of claim 16, wherein the reactant gas further comprises Ar gas.

18. (Original) The method of claim 13, wherein the high-resistant substrate is dry etched using a reaction gas comprising at least Cl_2 or BCl_3.

19. (Original) The method of claim 18, wherein the reactant gas further comprises Ar gas.

20. (Original) The method of claim 13, wherein the high-resistant substrate is etched to form a via hole through which the bottom of the first compound semiconductor layer is exposed.

21. (Previously Presented) The method of claim 13, wherein the high-resistant substrate is etched to expose a portion of the bottom of the first compound semiconductor layer that is larger than a portion of the first compound semiconductor layer that remains in contact with the high-resistant substrate after etching.

22. (Original) The method of claim 12, further comprising forming a pad layer on the light-transmitting conductive layer.

23-35. (Cancelled)